

Up to 6 GHz Medium Power Silicon Bipolar Transistor

Technical Data

Features

- **High Output Power:**
20.5 dBm Typical $P_{1\text{dB}}$ at 2.0 GHz
- **High Gain at 1 dB Compression:**
13.5 dB Typical $G_{1\text{dB}}$ at 2.0 GHz
- **Low Noise Figure:**
1.9 dB Typical NF_0 at 2.0 GHz
- **High Gain-Bandwidth Product:** 8.0 GHz Typical f_T
- **Surface Mount Plastic Package**
- **Tape-and-Reel Packaging Option Available⁽¹⁾**

Description

Hewlett-Packard's AT-42086 is a general purpose NPN bipolar transistor that offers excellent high frequency performance. The AT-42086 is housed in a low cost surface mount .085" diameter

Note:

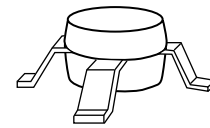
1. Refer to PACKAGING section "Tape-and-Reel Packaging for Semiconductor Devices."

plastic package. The 4 micron emitter-to-emitter pitch enables this transistor to be used in many different functions. The 20 emitter finger interdigitated geometry yields a medium sized transistor with impedances that are easy to match for low noise and medium power applications. Applications include use in wireless systems as an LNA, gain stage, buffer, oscillator, and mixer. An optimum noise match near $50\ \Omega$ up to 1 GHz, makes this device easy to use as a low noise amplifier.

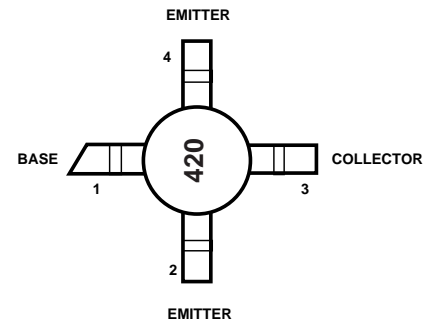
The AT-42086 bipolar transistor is fabricated using Hewlett-Packard's 10 GHz f_T Self-Aligned-Transistor (SAT) process. The die is nitride passivated for surface protection. Excellent device uniformity, performance and reliability are produced by the use of ion-implantation, self-alignment techniques, and gold metalization in the fabrication of this device.

AT-42086

86 Plastic Package



Pin Connections



AT-42086 Absolute Maximum Ratings

Symbol	Parameter	Units	Absolute Maximum ^[1]
V _{EBO}	Emitter-Base Voltage	V	1.5
V _{CB0}	Collector-Base Voltage	V	20
V _{CEO}	Collector-Emitter Voltage	V	12
I _C	Collector Current	mA	80
P _T	Power Dissipation ^[2,3]	mW	500
T _j	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to 150

Thermal Resistance^[2,4]:

$$\theta_{jc} = 140^{\circ}\text{C}/\text{W}$$

Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2. T_{CASE} = 25°C.
3. Derate at 7.1 mW/°C for T_C > 80°C.
4. See MEASUREMENTS section "Thermal Resistance" for more information.

Part Number Ordering Information

Part Number	Increment	Comments
AT-42086-BLK	100	Bulk
AT-42086-TR1	1000	Reel

Note: For more information, see "Tape and Reel Packaging for Semiconductor Devices".

Electrical Specifications, T_A = 25°C

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
S _{21E} ²	Insertion Power Gain; V _{CE} = 8 V, I _C = 35 mA	f = 1.0 GHz f = 2.0 GHz f = 4.0 GHz	dB	15.0	16.5 10.5 4.5
P _{1dB}	Power Output @ 1 dB Gain Compression V _{CE} = 8 V, I _C = 35 mA	f = 2.0 GHz f = 4.0 GHz	dBm		20.5 20.0
G _{1dB}	1 dB Compressed Gain; V _{CE} = 8 V, I _C = 35 mA	f = 2.0 GHz f = 4.0 GHz	dB		13.5 9.0
NF _O	Optimum Noise Figure; V _{CE} = 8 V, I _C = 10 mA	f = 2.0 GHz f = 4.0 GHz	dB		1.9 3.5
G _A	Gain @ NF _O ; V _{CE} = 8 V, I _C = 10 mA	f = 2.0 GHz f = 4.0 GHz	dB		13.0 9.0
f _T	Gain Bandwidth Product: V _{CE} = 8 V, I _C = 35 mA		GHz		8.0
h _{FE}	Forward Current Transfer Ratio; V _{CE} = 8 V, I _C = 35 mA		—	30	150
I _{CB0}	Collector Cutoff Current; V _{CB} = 8 V		μA		0.2
I _{EBO}	Emitter Cutoff Current; V _{EB} = 1 V		μA		2.0
C _{CB}	Collector Base Capacitance ^[1] : V _{CB} = 8 V, f = 1 MHz		pF	0.32	

Note:

1. For this test, the emitter is grounded.

AT-42086 Typical Performance, $T_A = 25^\circ\text{C}$

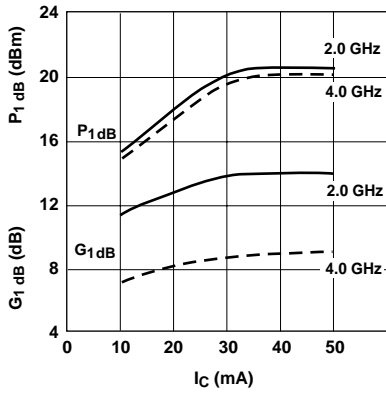


Figure 1. Output Power and 1 dB Compressed Gain vs. Collector Current and Frequency. $V_{CE} = 8\text{ V}$.

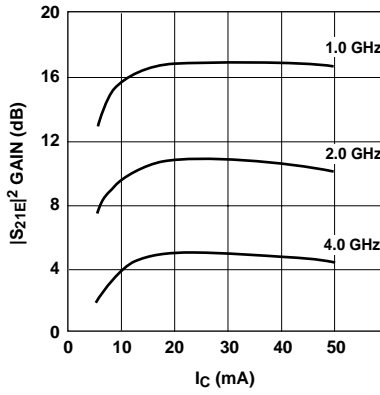


Figure 2. Insertion Power Gain vs. Collector Current and Frequency. $V_{CE} = 8\text{ V}$.

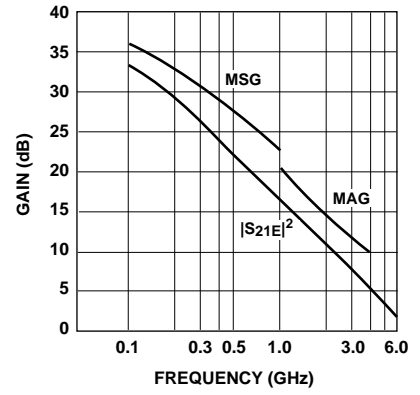


Figure 3. Insertion Power Gain, Maximum Available Gain and Maximum Stable Gain vs. Frequency. $V_{CE} = 8\text{ V}$, $I_C = 35\text{ mA}$.

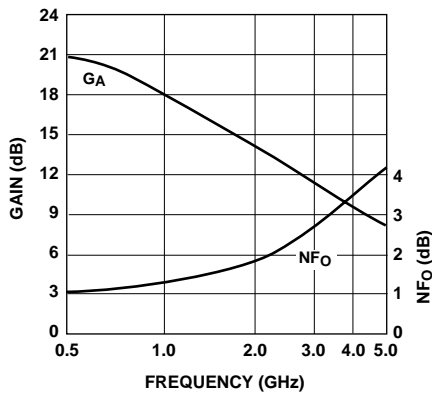


Figure 4. Noise Figure and Associated Gain vs. Frequency. $V_{CE} = 8\text{ V}$, $I_C = 10\text{ mA}$.

AT-42086 Typical Scattering Parameters,

Common Emitter, $Z_0 = 50 \Omega$, $T_A = 25^\circ\text{C}$, $V_{CE} = 8\text{V}$, $I_C = 10\text{mA}$

Freq. GHz	S_{11}		dB	S_{21}		dB	S_{12}		S_{22}	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
0.1	.68	-48	28.0	25.12	153	-36.0	.016	65	.91	-15
0.5	.63	-141	20.9	11.07	102	-29.9	.032	42	.54	-30
1.0	.63	-176	15.4	5.87	80	-27.4	.043	43	.43	-30
1.5	.65	164	12.0	3.98	65	-26.0	.050	46	.40	-34
2.0	.66	151	9.5	2.99	53	-23.9	.064	52	.38	-40
2.5	.69	142	7.8	2.44	45	-23.1	.070	53	.36	-46
3.0	.71	132	6.2	2.04	34	-21.6	.084	54	.34	-54
3.5	.73	123	4.8	1.74	24	-19.7	.104	53	.33	-67
4.0	.75	115	3.6	1.51	14	-18.3	.122	51	.30	-80
4.5	.78	108	2.6	1.34	5	-17.2	.138	50	.31	-94
5.0	.80	101	1.6	1.20	-4	-16.0	.159	46	.31	-110
5.5	.82	95	0.6	1.08	-12	-14.8	.182	40	.32	-129
6.0	.85	89	-0.2	0.97	-21	-14.0	.200	35	.34	-148

AT-42086 Typical Scattering Parameters,

Common Emitter, $Z_0 = 50 \Omega$, $T_A = 25^\circ\text{C}$, $V_{CE} = 8\text{V}$, $I_C = 35\text{mA}$

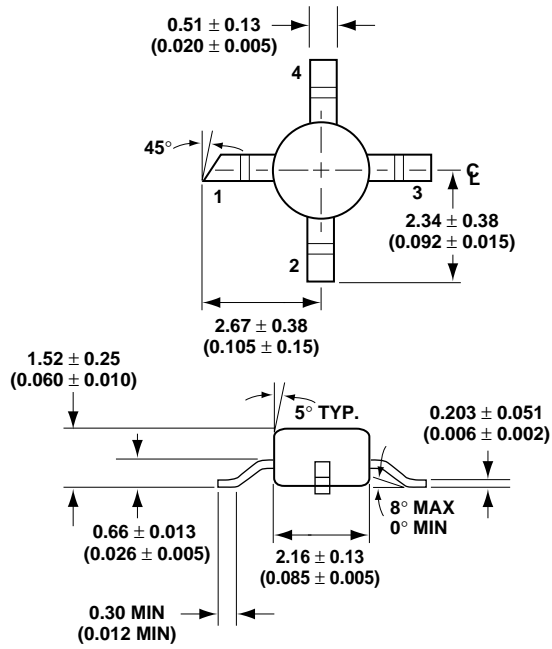
Freq. GHz	S_{11}		dB	S_{21}		dB	S_{12}		S_{22}	
	Mag.	Ang.		Mag.	Ang.		Mag.	Ang.	Mag.	Ang.
0.1	.48	-94	32.8	43.62	137	-37.7	.013	65	.77	-25
0.5	.57	-168	22.4	13.21	92	-32.6	.023	57	.39	-28
1.0	.59	168	16.5	6.69	75	-28.7	.037	62	.33	-27
1.5	.61	154	13.0	4.48	62	-24.8	.057	64	.31	-31
2.0	.63	143	10.5	3.36	51	-23.0	.071	61	.29	-37
2.5	.68	137	8.7	2.72	43	-21.0	.089	56	.26	-45
3.0	.68	127	7.0	2.25	33	-19.7	.104	58	.25	-53
3.5	.71	118	5.7	1.92	24	-18.4	.121	55	.24	-65
4.0	.73	111	4.5	1.69	14	-17.3	.136	49	.20	-80
4.5	.76	104	3.5	1.49	5	-15.9	.161	46	.21	-95
5.0	.78	98	2.4	1.32	-3	-15.2	.174	43	.21	-115
5.5	.81	91	1.6	1.20	-12	-14.3	.193	36	.22	-136
6.0	.84	85	0.7	1.08	-20	-13.4	.213	31	.25	-156

A model for this device is available in the DEVICE MODELS section.

AT-42086 Noise Parameters: $V_{CE} = 8\text{V}$, $I_C = 10\text{mA}$

Freq. GHz	NF_0 dB	Γ_{opt}		$R_N/50$
		Mag	Ang	
0.1	1.0	.04	8	0.13
0.5	1.1	.03	62	0.12
1.0	1.5	.06	168	0.12
2.0	1.9	.25	-146	0.12
4.0	3.5	.58	-100	0.52

86 Plastic Package Dimensions



DIMENSIONS ARE IN MILLIMETERS (INCHES)